

MEDIUM POWER DISCRETE SIGE TRANSISTOR



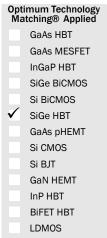
Package: SOT-89

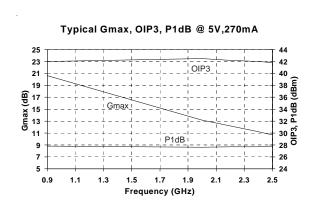


Product Description

RFMD's SGA9289Z is a high performance transistor designed for operation to 3GHz. With optimal matching at 2GHz, $OIP_3 = 42.5 dBm$, and $P_{1dB} = 27.5 dBm$. This RF device is based on a Silicon Germanium Heterostructure Bipolar Transistor (SiGe HBT) process. The SGA9289Z is cost-effective for applications requiring high linearity even at moderate biasing levels. It is well suited for operation at both 5V and 3V. The matte tin finish on the lead-free package utilizes a post annealing process to mitigate tin whisker formation and is RoHS compliant per EU Directive 2002/95. This package is also manufactured with green molding compounds that

contain no antimony trioxide nor halogenated fire retardants.





Features

- 50 MHz to 3000 MHz Operation
- 42.5dBm Output IP₃ Typ. at 1.96GHz
- 12.0dB Gain Typ. at 1.96GHz
- 27.5 dBm P_{1dB} Typ. at 1.96 GHz
- 2.4dB NF Typ. at 0.9GHz
- Cost-Effective
- 3V to 5V Operation

Applications

- Wireless Infrastructure Driver **Amplifiers**
- CATV Amplifiers
- Wireless Data, WLL Amplifiers
- AN-022 Contains Detailed Application Circuits

Parameter	Specification			Unit	Condition		
Parameter	Min.	Тур.	Max.	UIIIL	Condition		
Maximum Available Gain		20.5		dB	900 MHz, Z _S =Z _S *, Z _L =Z _L *		
		13.1		dB	1960MHz		
Power Gain	16.2	17.7	19.2	dB	900 MHz [1], Z _S =Z _{SOPT} , Z _L =Z _{LOPT}		
	11.0	12.0	13.0	dB	1960MHz [2]		
Output Power at 1dB Compression		28.0		dBm	900MHz, Z _S =Z _{SOPT} , Z _L =Z _{LOPT}		
	26.0	27.5		dBm	1960MHz [2]		
Output Third Order Intercept Point		42.0		dBm	900 MHz, Z _S =Z _{SOPT} , Z _L =Z _{LOPT} , P _{OUT} =+13dBm per tone		
	40.0	42.5		dBm	1960MHz [2]		
Noise Figure		2.4		dB	900MHz, Z _S =Z _{SOPT} , Z _L =Z _{LOPT}		
		2.5		dB	1960MHz		
DC Current Gain	100	180	300				
Breakdown Voltage	7.5	8.5		V	collector - emitter		
Thermal Resistance		32		°C/W	junction - lead		
Device Operating Voltage			5.5	V	collector - emitter		
Operating Current	250	280	320	mA			

Test Conditions: $V_{CE}=5V$, $I_{CQ}=280 \, \text{mA}$ (unless otherwise noted), $T_L=25 \, ^{\circ}\text{C}$. [1] 100% Tested [2] Sample Tested



Absolute Maximum Ratings

Parameter	Rating	Unit
Max Base Current (I _B)	10	mA
Max Device Current (I _{CE})	400	mA
Max Collector-Emitter Voltage (V _{CEO})	7	V
Max Collector-Base Voltage (V _{CBO})	20	V
Max Emitter-Base Voltage (V _{EBO})	4.8	V
Max Junction Temp (T _J)	+150	°C
Operating Temp Range (T _L)	See Graph	
Max Storage Temp	+150	°C

^{*}Note: Load condition1, $Z_L = 50 \Omega$.

Operation of this device beyond any one of these limits may cause permanent damage. For reliable continuous operation, the device voltage and current must not exceed the maximum operating values specified in the table on page one. Bias Conditions should also satisfy the following expression: $I_DV_D < (T_J - T_L) / R_{TH}, j - I \text{ and } T_L = T_{LEAD}$



Caution! ESD sensitive device.

Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional operation of the device under Absolute Maximum Rating conditions to the device may reduce the device under Absolute Maximum Rating conditions to the device may reduce the device under Absolute Maximum Rating conditions to the device may reduce the device under Absolute Maximum Rating conditions to the device under Abso tions is not implied.

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RFMD Green; RoHS compliant per EU Directive 2002/95/EC, halogen free per IEC 61249-2-21, < 1000 ppm each of antimony trioxide in polymeric materials and red phosphorus as a flame retardant, and <2% antimony in

Typical Performance with Engineering Application Circuit

Freq (MHz)	VCE (V)	ICQ (mA)	P1dB (dBm)	OIP3 ¹ (dBm)	Gain (dB)	S11 (dB)	S22 (dB)	NF (dB)	ZSOPT (Ω)	ZLOPT (Ω)
945	5	287	27.8	42.0	17.8	-19	-11	2.5	2.93 - j3.92	15.81 + j1.57
1960	5	292	27.5	42.0	12.1	-24	-21	2.5	4.75 - j9.12	10.3 - j4.87
2140	5	293	27.7	42.0	11.1	-11	-20	2.8	4.30 - j9.09	13.4 + j2.31
2440	5	287	27.5	42.0	9.8	-17	-20	3.0	4.05 - j13.78	11.76 - j9.2

 $^{^{1}}$ P_{OUT}=+13dBm per tone for V_{CE}=5V, 1MHz tone spacing

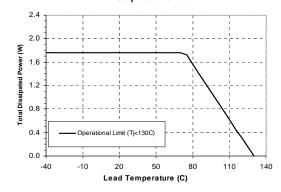
Typical Performance with Engineering Application Circuit

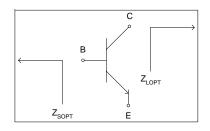
Freq (MHz)	VCE (V)	ICQ (mA)	P1dB (dBm)	OIP3 ² (dBm)	Gain (dB)	S11 (dB)	S22 (dB)	NF (dB)	ZSOPT (Ω)	ZLOPT (Ω)
945	3	312	25.4	38.6	16.8	-18	-9	2.6	5.61 - j4.75	6.51 + j2.58
1960	3	315	26.0	39.3	11.0	-18	-15	2.9	3.23 - j5.67	4.95 + j1.73
2440	3	315	26.1	38.0	9.4	-29	-17	3.4	4.07 - 14.25	11.62 - j11.83

 $^{^{2}}$ P_{OUT}=+10dBm per tone for V_{CE}=3V, 1MHz tone spacing

Data above represents typical performance of the application circuits notes in Application Note AN-022. Refer to the application note for additional RF data, PCB layouts, and BOMs for each application circuit. The application note also includes biasing instructions and other key issues to be considered. For the latest application notes please visit our site at wwww.RFMD.com or call your local sales representative.

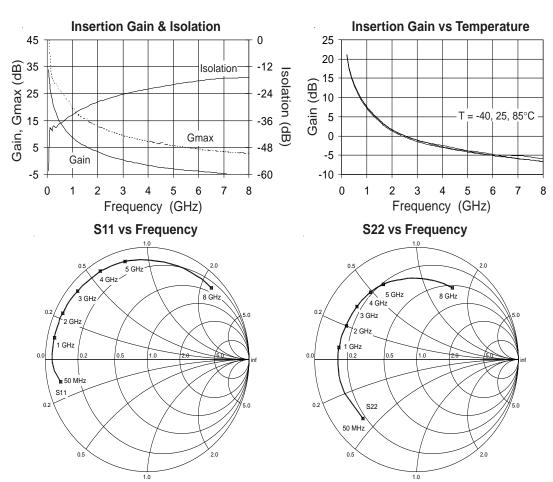
Maximum Recommended Operational **Dissipated Power**



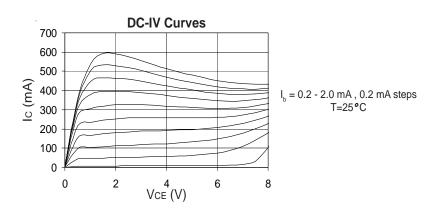




De-embedded S-Parameters (Z_s = Z_L =50 Ohms, V_{ce} =5V, I_{cq} =270mA, 25° C)



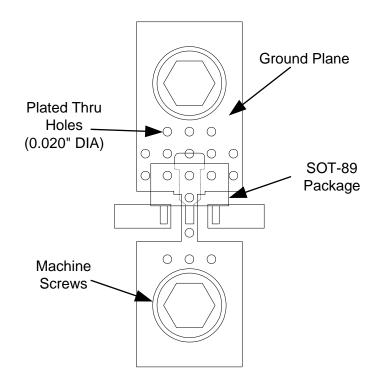
Note: S-parameters are de-embedded to the device leads with $Z_s = Z_L = 50\Omega$. The data represents typical performace of the device. De-embedded s-parameters can be downloaded from our website





Pin	Function	Description
1	Base	RF input.
2	Emitter	Connection to ground. Use via holes to reduce lead inductance. Place vias as close to ground leads as possible.
3	Collector	RF output.
4	Emitter	Same as pin 2.

Recommended Mounting Configuration for Optimum RF and Thermal Performance



Mounting and Thermal Considerations

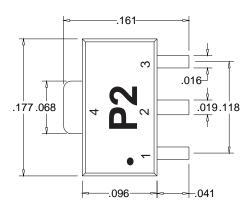
It is very important that adequate heat sinking be provided to minimize the device junction temperature. The following items should be implemented to maximize MTTF and RF performance.

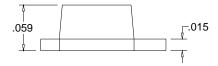
- 1. Multiple solder-filled vias are required directly below the ground tab (pin 4). [CRITICAL]
- 2. Incorporate a large ground pad area with multiple plated-through vias around pin 4 of the device. [CRITICAL]
- 3. Use two point board seating to lower the thermal resistance between the PCB and mounting plate. Place machine screws as close to the ground tab (pin 4) as possible. [RECOMMENDED]
- 4. Use 2 ounce copper to improve the PCB's heat spreading capability. [RECOMMENDED]



Package Drawing

Dimensions in inches (millimeters)
Refer to drawing posted at www.rfmd.com for tolerances.





Part Symbolization

The part will be symbolized with the "P2" ("P2Z" for RoHS version) designator and a dot signifying pin 1 on the top surface of the package. Alternate marking: "SGA9289Z" on line one with Trace Code on line two.

Ordering Information

Part Number	Description				
SGA9289Z	13" Reel with 3000 pieces				
SGA9289ZSQ	Sample Bag with 25 pieces				
SGA9289ZSR	7" Reel with 100 pieces				
SGA9289Z-EVB1	880 MHz, 5V Operation PCBA				
SGA9289Z-EVB2	2440 MHz, 5V Operation PCBA				